Raytheon continues research, development, production and integration of the world’s highest performing and most reliable GaN technology.

**2017 GaN INTEGRATION HIGHLIGHTS**

- AMDR
- EASR
- AN/TPY-2
- NGJ

**INNOVATION**
- 2009: Office of the Secretary of Defense Awards Raytheon for 2nd Defense Production Act Title III
- 2015: Raytheon wins prestigious AVIATION WEEK LAUREATE AWARD for our innovation in incorporating GaN into military radars
- 2013: Office of the Secretary of Defense Awards Raytheon for successful completion of Defense Production Act Title III
- 2013: Achieved Manufacturing Readiness Level 8 - the highest level obtained by any defense industry organization
- 2013: 75% Chip Cost Reduction

**PRODUCTION**
- 2009: Raytheon released GaN for production in its 4 inch trusted compound semiconductor foundry
- 2008: GaN transition to production underway

**DEVELOPMENT**
- 2004-2008: GaN transistor improvement phase
- 2002-2004: GaN materials improvement phase
- 1999: Raytheon commences research in GaN

**RESEARCH**
- 2000: Raytheon fabricates its first GaN transistor

18 YEARS INNOVATION WITH GALLIUM NITRIDE